

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	1.8m $\Omega$ @10V	140A

### Feature

- Split Gate Trench Technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

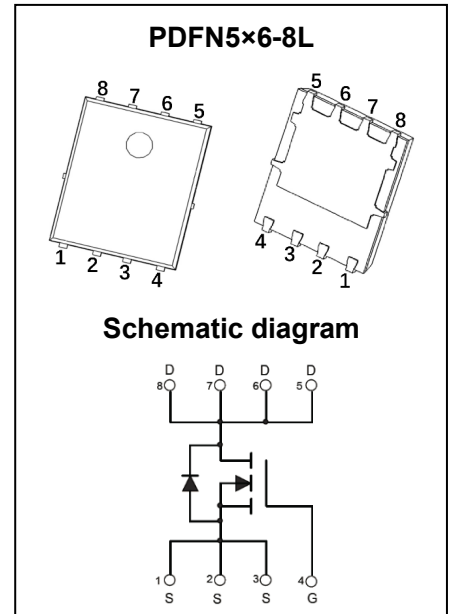
### Application

- Power Switching Application

### MARKING:



T026N06L = Device Code  
 XX = Date Code  
 Solid Dot = Green Indicator



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	60	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	140 A
	$T_C = 100^\circ\text{C}$	$I_D$	91 A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	560	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	55	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	756	mJ
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	93 W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	65	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.35	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

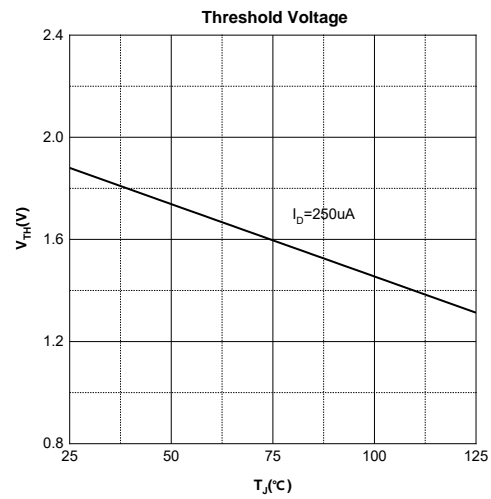
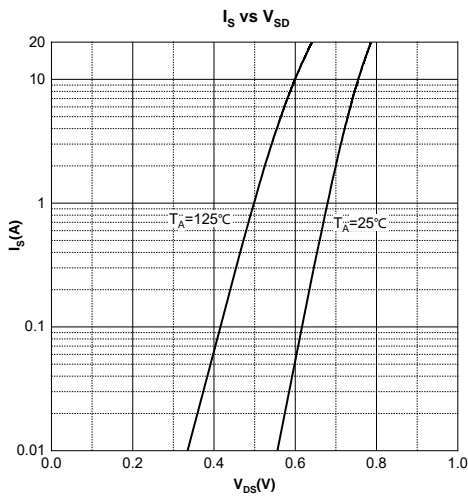
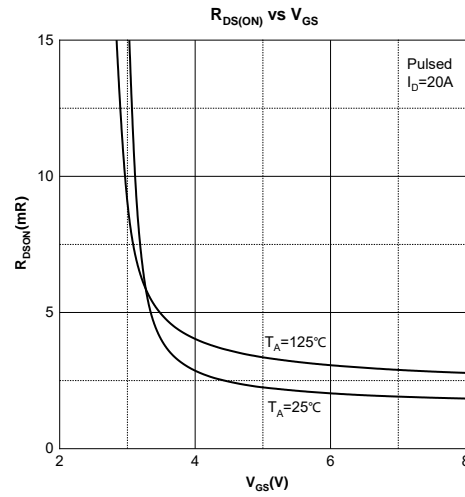
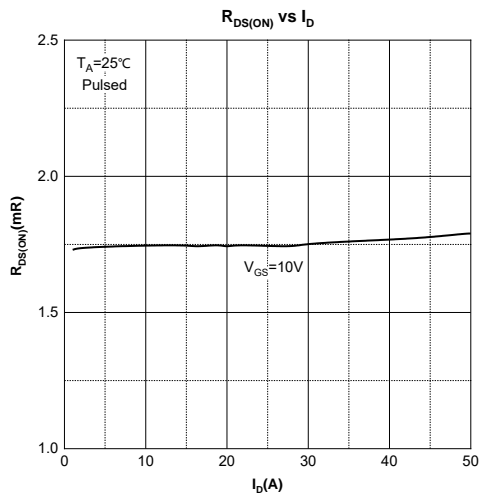
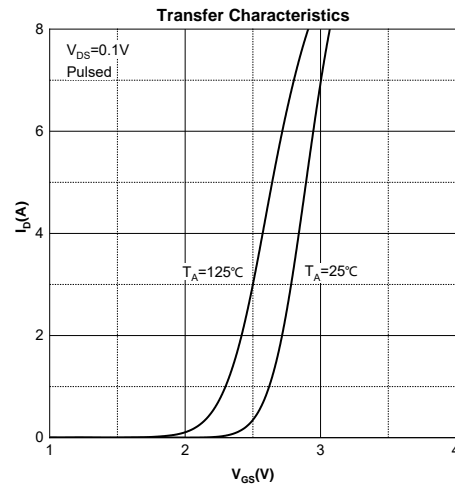
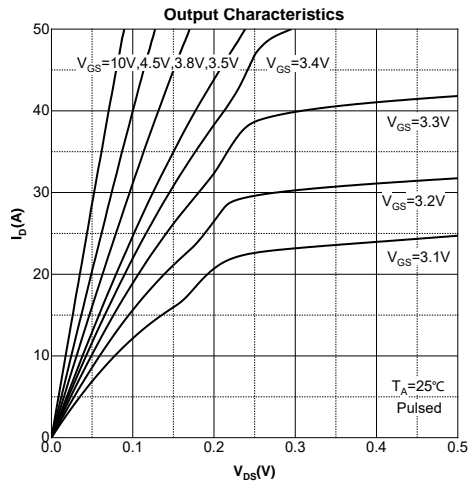
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

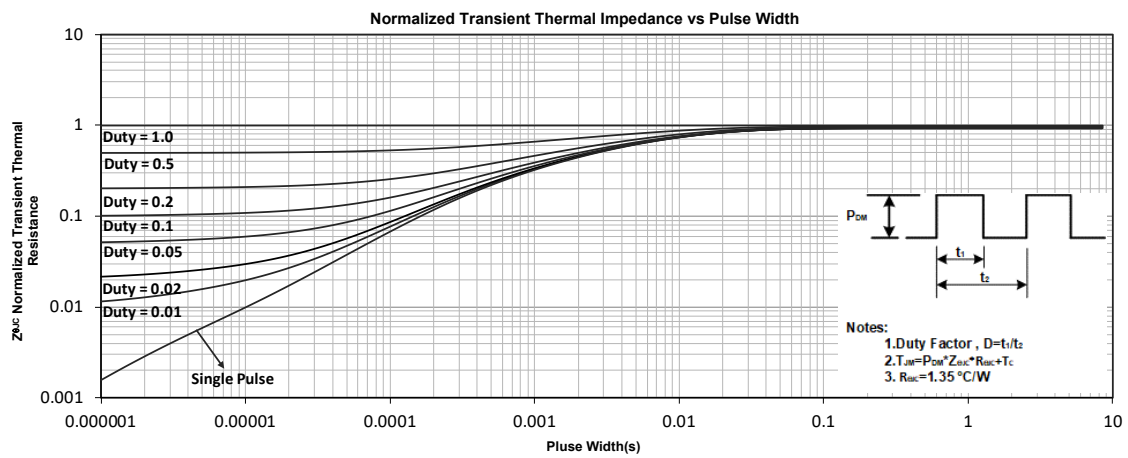
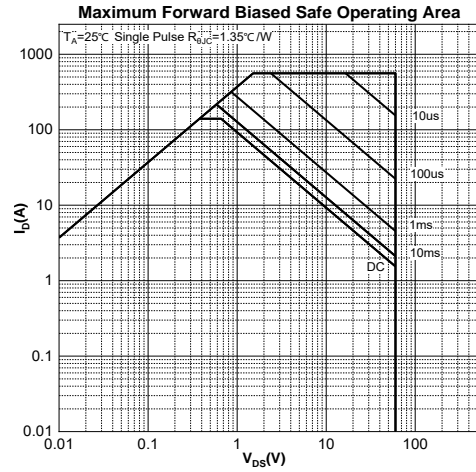
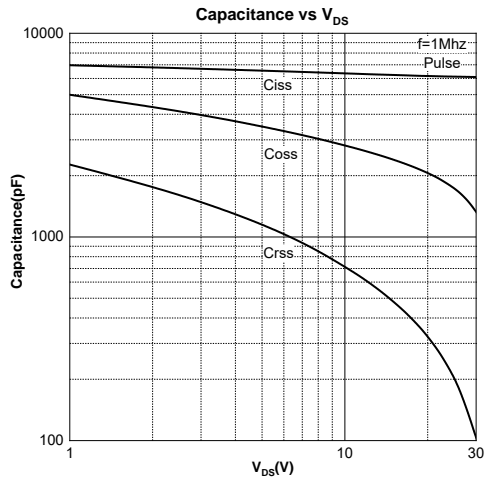
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.9	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		1.8	2.6	m $\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$		6101		pF
Output Capacitance	$C_{oss}$			1310		
Reverse Transfer Capacitance	$C_{rss}$			108		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.6		
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 30V, V_{GS} = 10V, I_D = 20A$		72		nC
Gate-source Charge	$Q_{gs}$			13		
Gate-drain Charge	$Q_{gd}$			16		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V, I_D = 20A,$ $R_G = 3\Omega$		11		ns
Turn-on Rise Time	$t_r$			6.5		
Turn-off Delay Time	$t_{d(off)}$			45		
Turn-off Fall Time	$t_f$			10		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 20A$			1.2	V

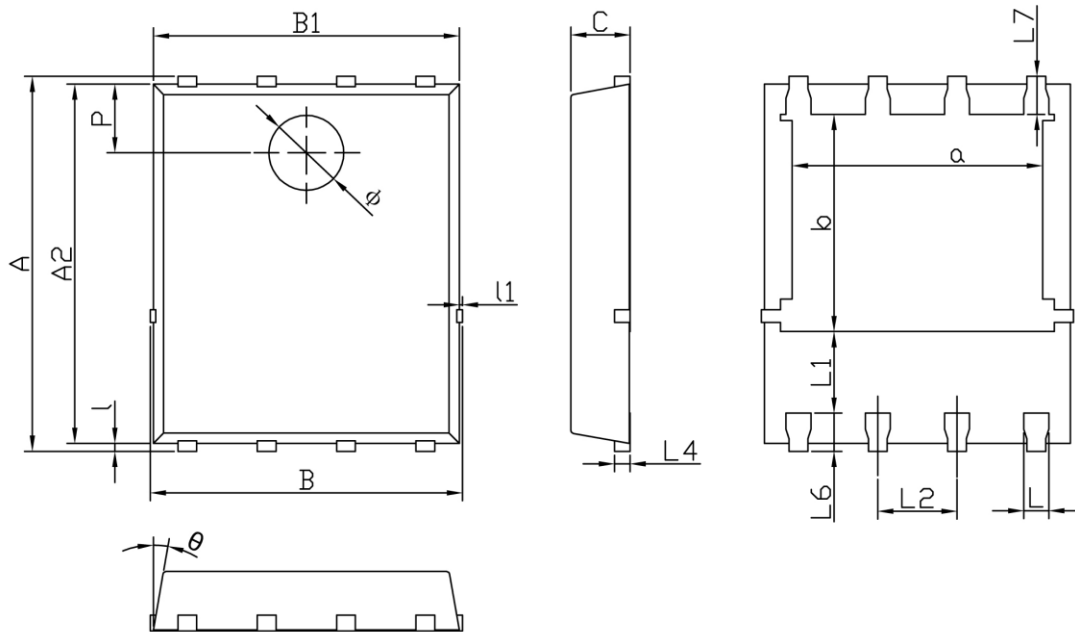
### Notes :

1. The maximum current rating is limited by package. And device mounted on a large heatsink
2. Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
3. EAS condition:  $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ . And device mounted on a large heatsink
6. Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## Typical Characteristics





**PDFN5×6-8L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.900	6.100	0.232	0.240
a	3.910	4.110	0.154	0.162
A2	5.700	5.800	0.224	0.228
B	4.900	5.100	0.193	0.201
b	3.370	3.570	0.133	0.141
B1	4.800	5.000	0.189	0.197
C	0.900	1.000	0.035	0.039
L	0.350	0.450	0.014	0.018
l	0.060	0.200	0.002	0.008
L1	1.100	-	0.043	-
l1	-	0.100	-	0.004
L2	1.170	1.370	0.046	0.054
L4	0.210	0.340	0.008	0.013
L6	0.510	0.710	0.020	0.028
L7	0.510	0.710	0.020	0.028
P	1.000	1.200	0.039	0.047
$\Phi$	1.100	1.300	0.043	0.051
$\theta$	8°	12°	8°	12°